

Silicon NPN Power Transistors

2SC2738

DESCRIPTION

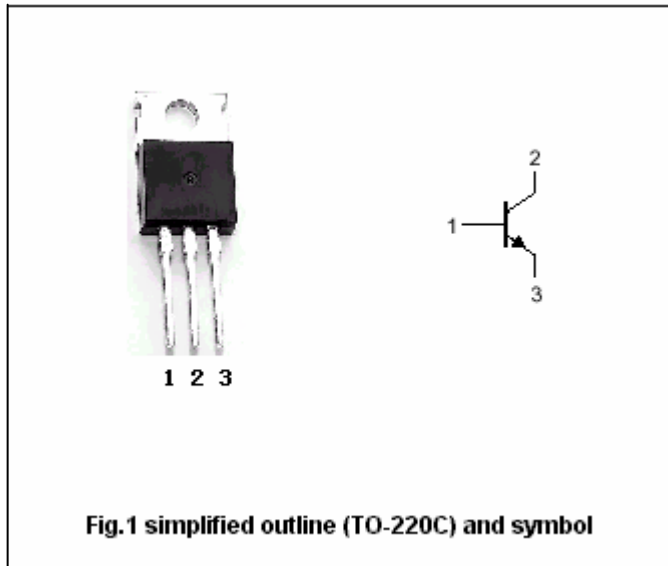
- With TO-220C package
- High speed switching
- High V_{CBO}
- Low saturation voltage

APPLICATIONS

- For high speed switching applications

PINNING

PIN DE	SCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL P	ARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current (DC)		2	A
I_{CM}	ollector current-Peak		4	A
I_B	Base current		0.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	25	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; L=25mH	400			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =1A; I _B =0.2A			1.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =1A; I _B =0.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE-1}	DC current gain	I _C =0.1A ; V _{CE} =5V 15				
h _{FE-2}	DC current gain	I _C =1A ; V _{CE} =5V 8				
f _T	Transition frequency	I _C =0.2 A ; V _{CE} =10V		11		MHz

Switching times

t _{on}	Turn-on time	V _{CC} =100V , I _C =1A, I _{B1} =-I _{B2} =0.2A			1.0	μs
t _s	Storage time				3.0	μs
t _f	Fall time				1.0 μ	s

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PACKAGE OUTLINE

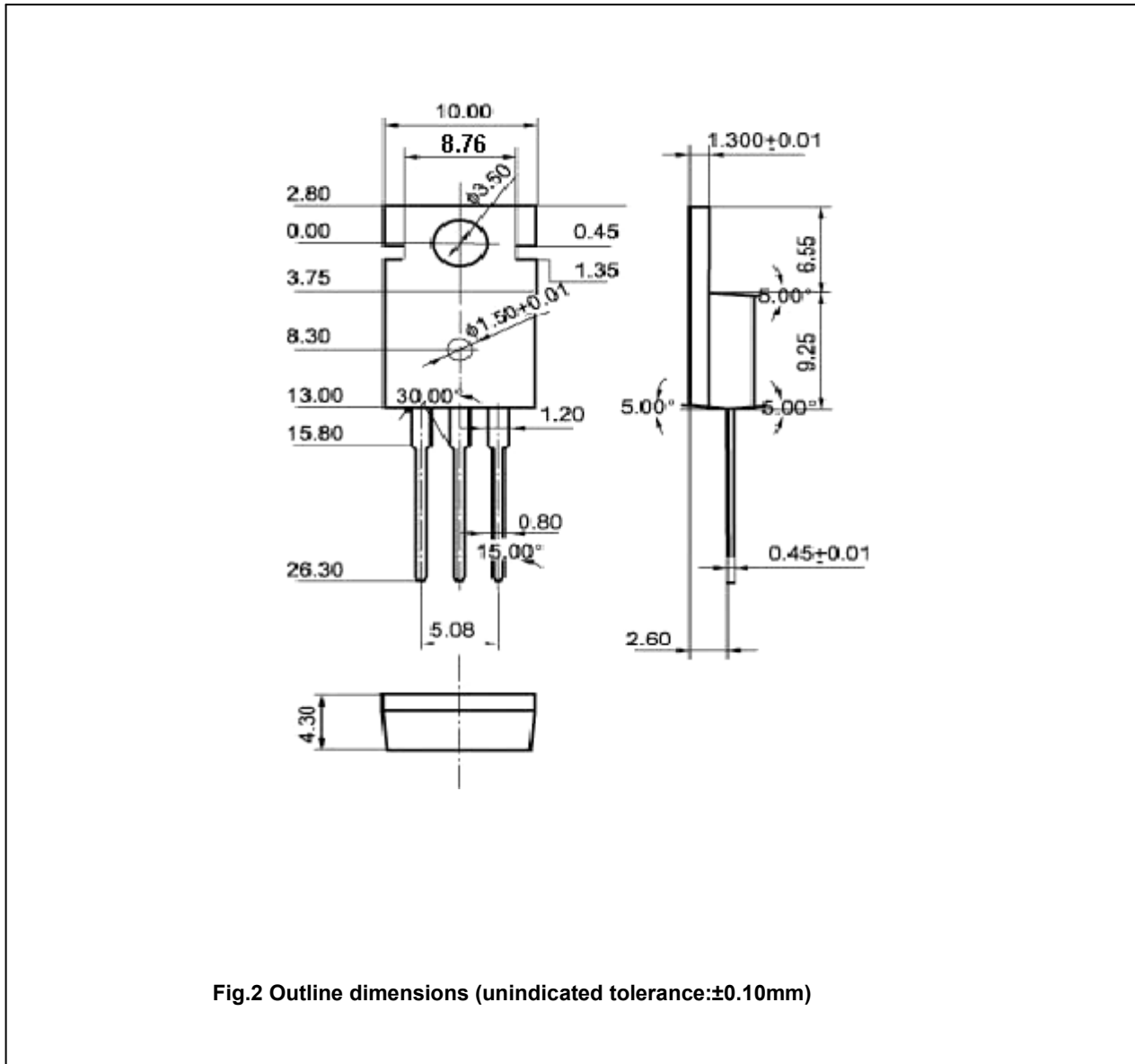


Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)